

・国際会議発表（招待講演は除く）

※査読付プロシードィングス

1. T. Akasaka, Y. Araki, and I. Shimizu\*, "In situ ellipsometric observation of the growth of crystalline silicon from fluorinated precursors", Material Research Society symposium proceedings (Amorphous Silicon Technology - 1993 Symposium), (1993) pp. 19-24. (IF=-), (Times Cited: 1)
2. S. Ishihara, D. He, T. Akasaka, Y. Araki, and I. Shimizu\*, "Fabrication of high quality Poly-Si from fluorinated precursors", Material Research Society symposium proceedings (Amorphous Silicon Technology - 1993 Symposium), (1993) pp. 79-89. (IF=-), (Times Cited: 7)
3. S. Ishihara, D. He, T. Akasaka, Y. Araki, M. Nakata, and I. Shimizu\*, "Highly textured microcrystalline-Si thin film fabricated by Layer-by-layer technique", Material Research Society symposium proceedings (Microcrystalline Semiconductors: Materials Science and Devices Symposium), (1993) pp. 489-494. (IF=-), (Times Cited: 3)
4. T. Akasaka and I. Shimizu\*, "Fabrication of high quality polysilicon thin films on glass and its in situ real-time monitoring by spectroscopic ellipsometry", 1994 IEEE First World Conference on Photovoltaic Energy Conversion. Conference Record of the Twenty Fourth IEEE Photovoltaic Specialists Conference-1994 **2**, (1994) pp. 1402-1405. (IF=-), (Times Cited: 1)
5. K. Nakamura, T. Akasaka, D. He, and I. Shimizu\*, "Control of grain size and texture of poly-Si with atomic hydrogen under in situ ellipsometric observation", Material Research Society symposium proceedings (Microcrystalline and Nanocrystalline Semiconductors. Symposium), (1995) pp. 871-876. (IF=-), (Times Cited: 0)
6. T. Akasaka, D. He, and I. Shimizu\*, "Fabrication of polycrystalline silicon on glass from fluorinated precursors with the aid of atomic hydrogen", Material Research Society symposium proceedings (Polycrystalline Thin Films: Structure, Texture, Properties, and Applications II. Symposium), (1996) pp. 391-396. (IF=-), (Times Cited: 1)
7. N. Kobayashi\*, T. Akasaka, S. Ando, and M. Kumagai, "Growth shape control of group-III nitrides by selective-area MOVPE", Proceedings of the SPIE - The International Society for Optical Engineering **3419**, (1998) pp. 2-6.
8. T. Akasaka\*, S. Ando, and N. Kobayashi, "Electroluminescence from p-GaN/n-InGaN MQW hexagonal microp Prism fabricated by selective area MOVPE", The Institute of Pure and Applied Physics (IPAP) Conf. Series **1**, (2000) pp.864-867. (IF=-), (Times Cited: 4)